

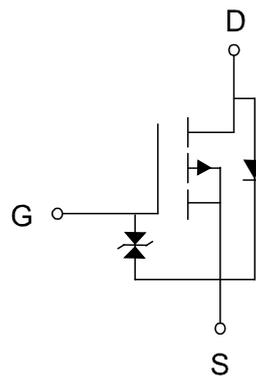
■ **Features**

- Surface Mount Package
- P-Channel Switch with Low RDS(on)
- Operated at Low Logic Level Gate Drive
- ESD Protected



V <sub>DSS</sub>	R <sub>DS(ON)</sub> @V <sub>GS</sub> =-4.5V	R <sub>DS(ON)</sub> @V <sub>GS</sub> =-2.5V	I <sub>D</sub>
-20V	0.8Ω	1.1Ω	-0.66A

■ **Schematic & PIN Configuration**



**SOT723**

■ **Absolute Maximum Ratings (T<sub>A</sub>=25°C unless otherwise noted)**

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	-20	V
Gate-Source Voltage	V <sub>GS</sub>	±12	V
Continuous Drain Current	I <sub>D</sub>	-0.66	A
Pulsed Drain Current	I <sub>DM</sub>	-1.2	A
Power Dissipation	P <sub>D</sub>	0.15	W
Thermal Resistance from Junction to Ambient	R <sub>θJA</sub>	833	°C/W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>STG</sub>	-55~ +150	°C

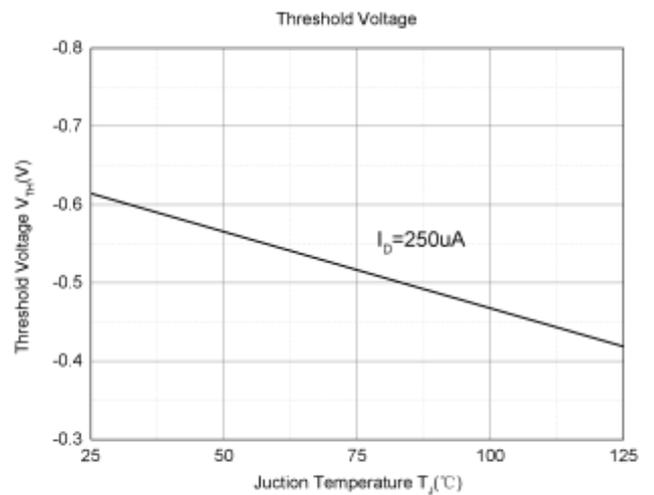
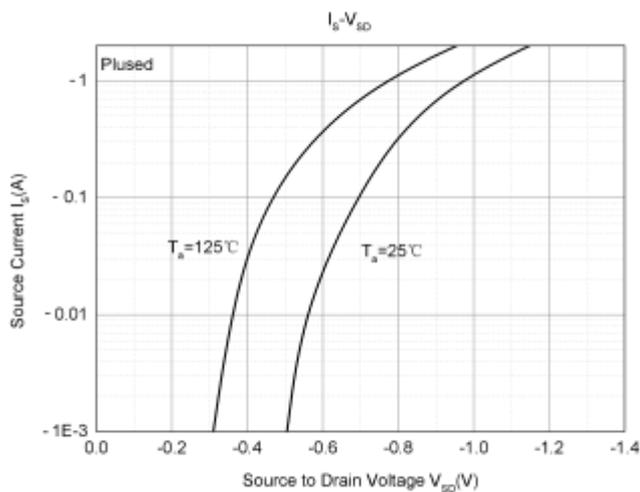
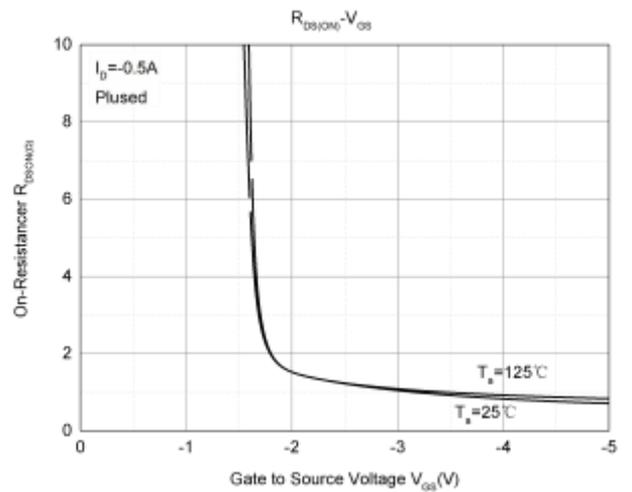
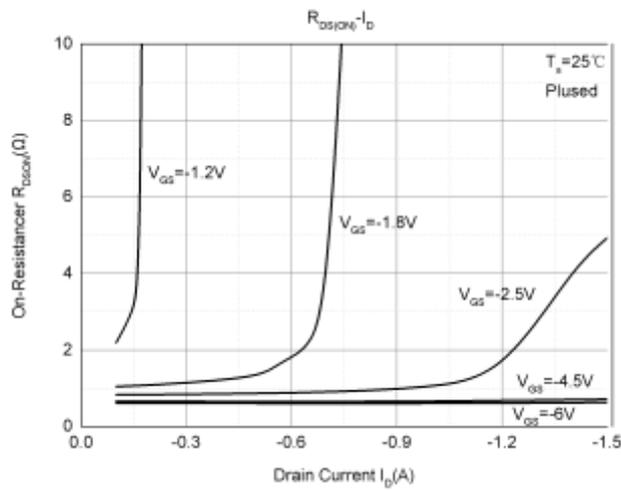
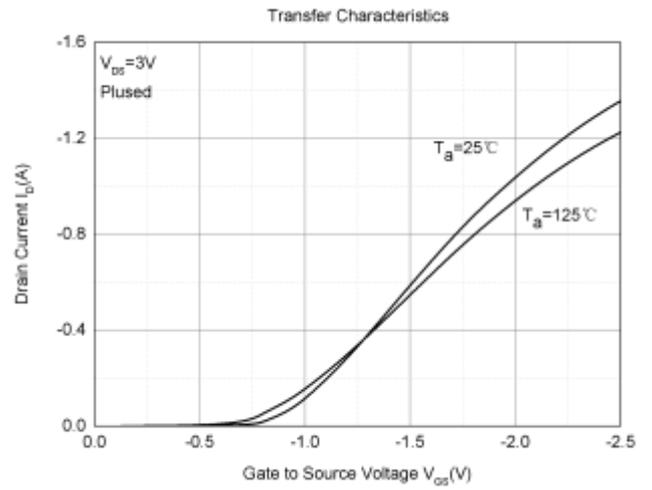
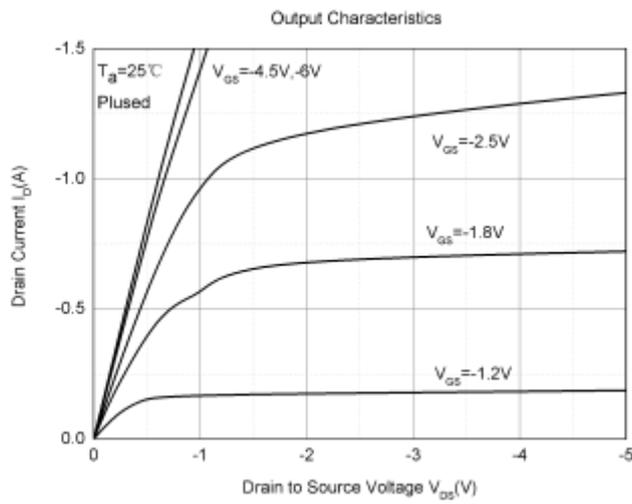
### ■ Electrical Characteristics ( $T_A = 25^\circ\text{C}$ unless otherwise noted )

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-20			V
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = -16V, V_{GS} = 0V$			-1	$\mu A$
Gate-body leakage current	$I_{GSS}$	$V_{GS} = \pm 10V, V_{DS} = 0V$			$\pm 10$	$\mu A$
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.35	-0.65	-1	V
Drain-source on-resistance <sup>1)</sup>	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -0.5A$		0.65	0.8	$\Omega$
		$V_{GS} = -2.5V, I_D = -0.2A$		0.85	1.1	
		$V_{GS} = -1.8V, I_D = -0.1A$		1.2		
<b>Dynamic characteristics<sup>2)</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = -16V, V_{GS} = 0V, f = 1MHz$		113		pF
Output Capacitance	$C_{oss}$			15		
Reverse Transfer Capacitance	$C_{rss}$			9		
Turn-on delay time	$t_{d(on)}$	$V_{DS} = -10V, I_D = -200mA,$ $V_{GS} = -4.5V, R_G = 10\Omega$		9		ns
Turn-on rise time	$t_r$			5.7		
Turn-off delay time	$t_{d(off)}$			32.6		
Turn-off fall time	$t_f$			20.3		
<b>Source-Drain Diode characteristics</b>						
Diode Forward voltage	$V_{SD}$	$V_{GS} = 0V, I_S = -0.5 A$			-1.2	V

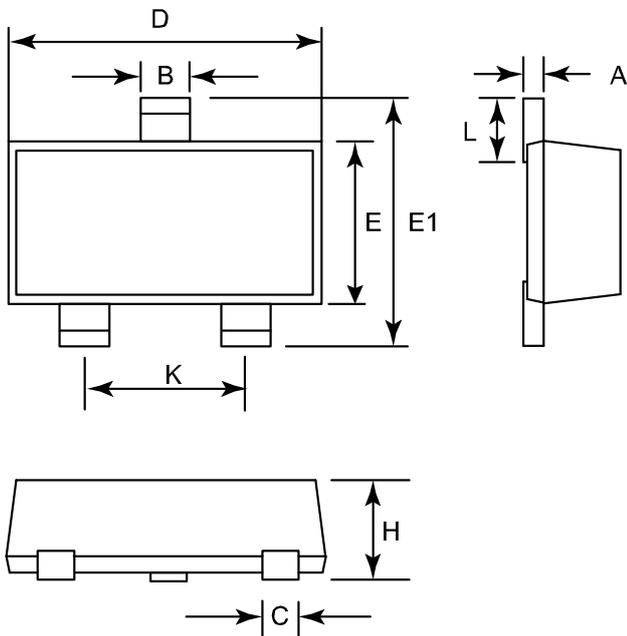
Notes:

- 1) Pulse Test: Pulse Width < 300 $\mu s$ , Duty Cycle  $\leq 2\%$ .
- 2) Guaranteed by design, not subject to production testing.

■ Typical Characteristics

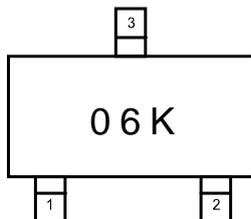


■ Outline Drawing SOT723



SYM	DIMENSIONS		
	MILLIMETERS		
	MIN	NOM	MAX
A	0.08		0.18
B	0.27		0.37
C	0.17		0.27
D	1.15	1.20	1.25
E	0.75	0.80	0.85
E1	1.15	1.20	1.25
K	0.75	0.80	0.85
L	0.25		0.30
H	0.43		0.55

Marking



Ordering information

Order code	Package	Base qty	Delivery mode
SE20P07M	SOT723	10k	Tape and reel

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